



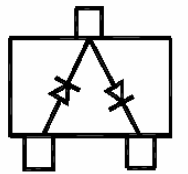
# TIGER ELECTRONIC CO.,LTD

## SOT-23 Plastic-Encapsulate Transistors

**1SS226** SWITCHING DIODE

### FEATURES

- Low forward voltage :  $V_F (3) = 0.9V$  (typ.)
- Fast reverse recovery time :  $t_{rr} = 1.6ns$  (typ.)
- Small total capacitance :  $C_T = 0.9pF$  (typ.)



**MARKING: C3**

**Maximum Ratings ,Single Diode @ $T_A=25^{\circ}C$**

Parameter	Symbol	Limits	Unit
Non-Repetitive Peak reverse voltage	$V_{RM}$	85	V
Peak Repetitive Peak reverse voltage	$V_{RRM}$	80	V
Working Peak Reverse Voltage	$V_{RWM}$		
DC Blocking Voltage	$V_R$		
Forward Continuous Current	$I_{FM}$	300	mA
Average Rectified Output Current	$I_O$	100	mA
Peak forward surge current @=10ms	$I_{FSM}$	2	A
Power Dissipation	$P_D$	150	mW
Junction temperature	$T_J$	150	$^{\circ}C$
Storage temperature	$T_{STG}$	-55-150	$^{\circ}C$

### ELECTRICAL CHARACTERISTICS ( $T_{amb}=25^{\circ}C$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Reverse breakdown voltage	$V_{(BR)}$	$I_R = 100\mu A$	80		V
Reverse voltage leakage current	$I_R$	$V_R = 80V$		0.5	$\mu A$
Forward voltage	$V_F$	$I_F = 100mA$		1.2	V
Diode capacitance	$C_D$	$V_R = 0V, f = 1MHz$		3	pF
Reverse recovery time	$t_{rr}$	$I_F = 10mA$		4	nS

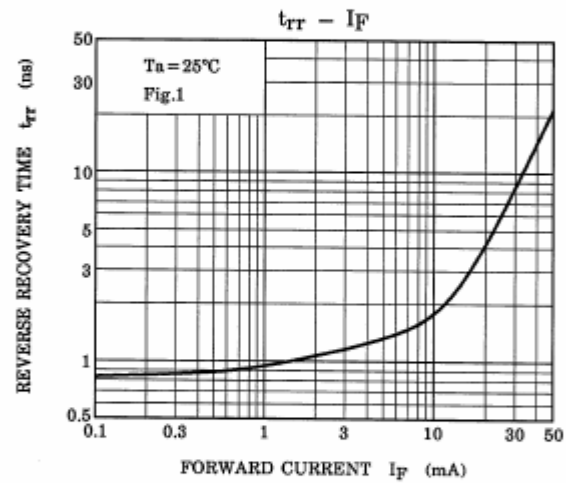
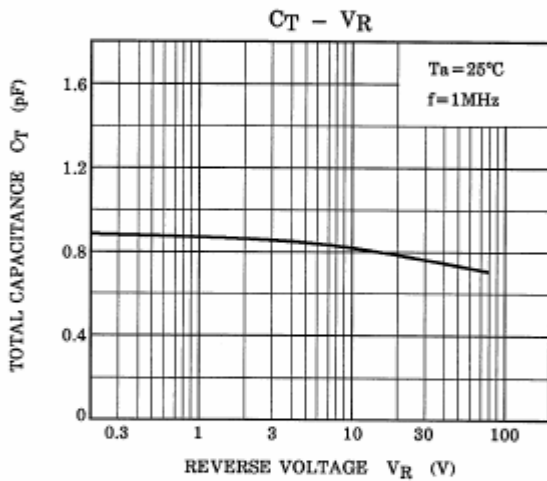
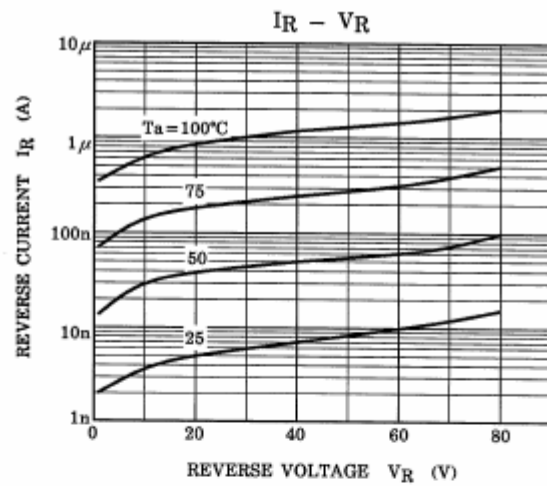
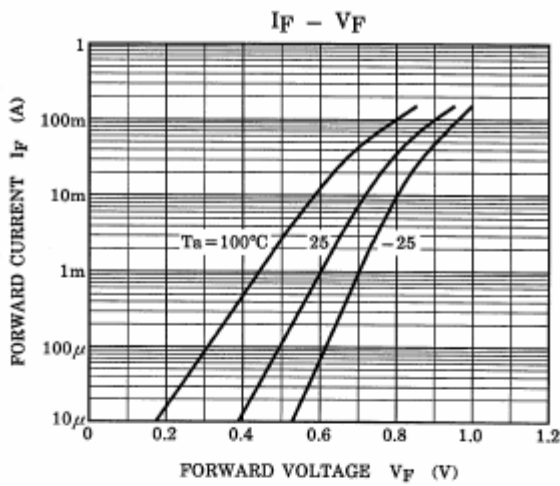


Fig.1 Reverse recovery time ( $t_{rr}$ ) test circuit

